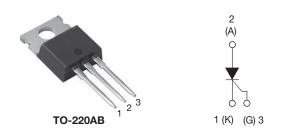
**Vishay Semiconductors** 

# High Voltage, Phase Control Thyristor, 12 A



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PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub> 8 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V						
V <sub>TM</sub>	1.2 V						
I <sub>GT</sub>	15 mA						
TJ	-40 to +125 °C						
Package	TO-220AB						
Circuit configuration	Single SCR						

### FEATURES

- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

### DESCRIPTION

The VS-12TTS08HM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А					

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	8	А						
I <sub>T(RMS)</sub>		12.5							
V <sub>RRM</sub> /V <sub>DRM</sub>		800	V						
I <sub>TSM</sub>		110	A						
V <sub>T</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V						
dV/dt		150	V/µs						
dl/dt		100	A/µs						
TJ	Range	-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> / I <sub>DRM</sub> AT 125 °C mA						
VS-12TTS08HM3	800	800	5.0						

(Pb) RoHS

COMPLIANT HALOGEN

# VS-12TTS08HM3



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ABSOLUTE MAXIMUM RATINGS	;			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T = 108 °C 180° conduction half size wave	8	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	$T_{C} = 108 \ ^{\circ}C$ , 180° conduction, half sine wave	12.5	А
Maximum peak one-cycle	<b>L</b>	10 ms sine pulse, rated $V_{RRM}$ applied, $T_J$ = 125 °C	95	A
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied, $T_J$ = 125 °C	110	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{RRM}$ applied, $T_J$ = 125 °C	45	A <sup>2</sup> s
	1-1	10 ms sine pulse, no voltage reapplied, $T_J$ = 125 °C	64	
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, $T_{J}$ = 125 $^{\circ}\text{C}$	640	A²√s
Maximum on-state voltage drop	V <sub>TM</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V
On-state slope resistance	r <sub>t</sub>	Т, <sub>1</sub> = 125 °С	16.2	mΩ
Threshold voltage	V <sub>T(TO)</sub>	13 - 123 0	0.87	V
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$T_J = 25 \degree C$ $V_B = rated V_{BBM} / V_{DBM}$	0.05	
Maximum reverse and direct leakage current	'RM' 'DM	$T_J = 125 \text{ °C}$	5.0	
Typical holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C	30	mA
Typical latching current	١L	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$ , linear to 80 %, $V_{DRM} = R_g - k = open$	150	V/µs
Maximum rate of rise of turned-on current	dl/dt		100	A∕µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv	
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	А	
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, $T_J = -65 \text{ °C}$	20	mA	
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	15		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	10		
		Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	1.2		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	1		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	0.7	V	
Maximum DC gate voltage not to trigger	V <sub>GD</sub>	T 105 °C V reteductue	0.2		
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	0.1	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	3	μs
Typical turn-off time	t <sub>q</sub>	1J = 123 0	100	



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THERMAL AND MECHANIC	THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.5						
Maximum thermal resistance, junction to ambient	R <sub>thJA</sub>		62	°C/W					
Typical thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.5						
Approximate weight			2	g					
Approximate weight			0.07	oz.					
Mounting torgue	minimum		6 (5)	kgf · cm					
	maximum		12 (10)	(lbf · in)					
Marking device		Case style TO-220AB	12TT	S08H					

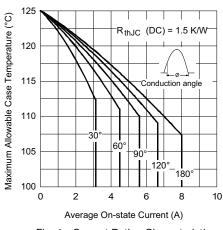
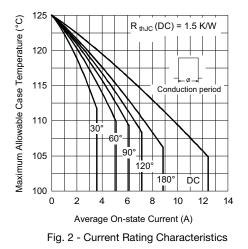


Fig. 1 - Current Rating Characteristics



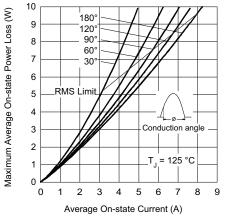


Fig. 3 - On-State Power Loss Characteristics

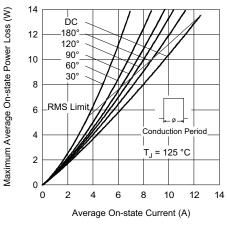
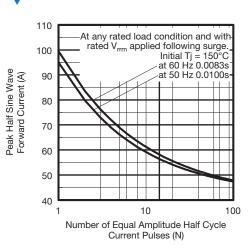


Fig. 4 - On-State Power Loss Characteristics

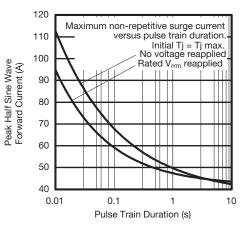
# VS-12TTS08HM3

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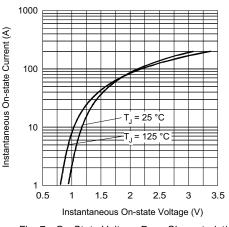


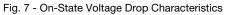
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Fig. 5 - Maximum Non-Repetitive Surge Current









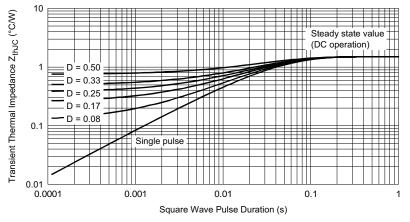


Fig. 8 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

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### **ORDERING INFORMATION TABLE**

Device code	VS-	12	т	т	S	08	н	М3
		2	3	4	5	6	7	8
	1 .	- Visl	hay Sen	nicondu	ctors pro	oduct		
	2 -	- Cur	rent rati	ng (12.5	5 A)			
	3 -	- Circ	cuit conf	iguratio	า:			
		T =	single t	nyristor				
	4 -	· Pac	kage:					
	_	T =	TO-220					
	5 -	. Тур	e of silio	con:				
		S =	standa	d recov	ery rect	ifier		
	6 -	· Vol	tage rati	ng (08 =	= 800 V)	)		
	7 -	• H=	AEC-Q	101 qua	lified			
	8	- Env	vironmer	ntal digit	:			
		М3	= halog	en-free,	RoHS-0	complia	nt, and	termina

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-12TTS08HM3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95222						
Part marking information	www.vishay.com/doc?95028					

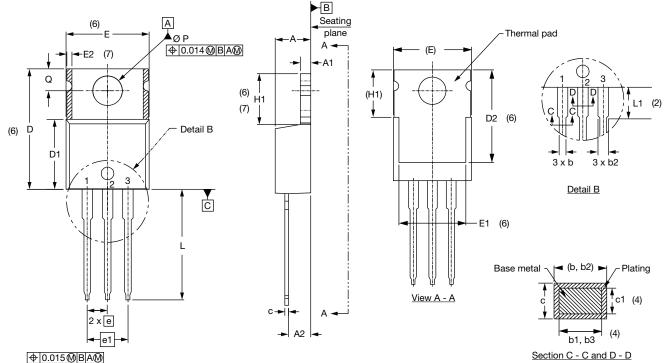
## **Outline Dimensions**



**Vishay Semiconductors** 

**TO-220AB** 

### **DIMENSIONS** in millimeters and inches



Lead tip

Conforms to JEDEC<sup>®</sup> outline TO-220AB

SYMBOL	MILLIMETERS		METERS INCHES		NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES	
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.56	2.92	0.101	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			E2	-	0.76	-	0.030	7
b1	0.38	0.97	0.015	0.038	4		е	2.41	2.67	0.095	0.105	
b2	1.20	1.73	0.047	0.068			e1	4.88	5.28	0.192	0.208	
b3	1.14	1.73	0.045	0.068	4		H1	5.84	6.86	0.230	0.270	6, 7
с	0.36	0.61	0.014	0.024			L	13.52	14.02	0.532	0.552	
c1	0.36	0.56	0.014	0.022	4		L1	3.32	3.82	0.131	0.150	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

<sup>(5)</sup> Controlling dimensions: inches

<sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1

<sup>(7)</sup> Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed

(8) Outline conforms to JEDEC<sup>®</sup> TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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